

Product Introduction

Our GaAs (Gallium Arsenide) wafers are single-crystal substrates grown using VGF or LEC methods, available in <100> and <111> orientations from 2" to 6" in diameter. Offered undoped or doped with Zn, Si, or Te, these wafers feature front-side surfaces polished in epi-ready prime grade, with mobility ranging from 1500 to 5000 cm²/V-sec depending on dopant type. Precision-controlled primary and secondary flats ensure accurate crystal orientation identification, making these wafers a reliable choice for demanding compound semiconductor applications.

Applications

- RF and microwave devices (power amplifiers, MMICs)
- LED and laser diode substrates
- High-efficiency solar cells (multi-junction and single-junction)
- High-electron-mobility transistors (HEMT) and heterojunction bipolar transistors (HBT)

GALLIUM ARSENIDE (GAAS) WAFER SPECIFICATION	
DIAMETER	50 ~ 150MM ± 0.25MM(2" 3" 4" 6")
Material	Single Crystal Gallium Arsenide
Growth Method	VGF / LEC Grown
Crystal Orientation	<100> / <111>
Crystal Orientation	$\alpha \pm \beta$, off angle α and accuracy β upon request
Dopant	Undoped / Zn / Si / Te
Thickness	350 ± 25um / 550 ± 25um / 625 ± 25um
Mobility	1500 ~ 3000 / 3000 ~ 5000 cm ² / V·sec
Primary Flat	<0-1-1> ± 0.5deg, 16 ± 1.0mm / 22 ± 1.0mm / 32.5 ± 1.0mm
Secondary Flat	<0-1-1> ± 5.0 deg, 8 ± 1.0mm / 11 ± 1.0mm / 18 ± 1.0mm
Front-side	Polished in Epi-ready Prime grade
Back-side	Polished / Lapping or Etched
Epi-ready	Yes